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M. Braunson
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): COHEN et al.

Examiner: Louie, Wai S.

Serial No.: 09/502,729

Group Art Unit: 2814

Filed: February 11, 2000

Docket: 728-163 (YO999-573)

For: DIFFUSION BARRIER LAYER AND
SEMICONDUCTOR DEVICE CONTAINING SAME

Dated: August 6, 2002

Box Non-Fee Amendment

Commissioner for Patents
Washington, D.C. 20231

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AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated May 6, 2002, please consider the following amendments and remarks.

IN THE CLAIMS:

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1. (Amended) A diffusion barrier layer for semiconductor devices, the diffusion barrier layer having an upper surface and a lower surface and a central portion and comprising silicon, carbon, nitrogen and hydrogen, with the nitrogen being non-uniformly distributed throughout the diffusion barrier layer, wherein the central portion is substantially devoid of nitrogen.

 2. (Amended) The diffusion barrier layer of Claim 1 wherein the upper

CERTIFICATE OF MAILING UNDER 37 C.F.R. § 1.8 (a)

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail, postpaid in an envelope, addressed to the: Box Non-Fee Amendment, Commissioner for Patents, Washington, DC 20231, on August 6, 2002.

Dated: August 6, 2002

Paul J. Farrell